1. General description

The 74LVC1G125 provides one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (\overline{OE}). A HIGH-level at pin \overline{OE} causes the output to assume a high-impedance OFF-state.

The input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8-B/JESD36 (2.7 V to 3.6 V)
- ± 24 mA output drive (V_{CC} = 3.0 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- CMOS low power consumption
- Inputs accept voltages up to 5 V
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

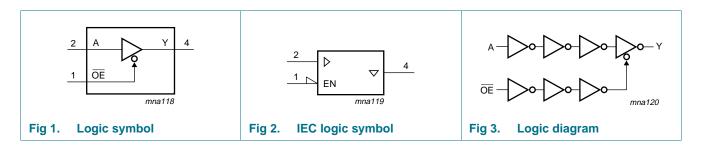
Table 1. Ordering information							
Package							
Version							
5 leads; SOT353-1							
s SOT753							
age; SOT886 5 mm							
age; SOT891 im							
leads; SOT1115							
leads; SOT1202							

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74LVC1G125GW	VM
74LVC1G125GV	V25
74LVC1G125GM	VM
74LVC1G125GF	VM
74LVC1G125GN	VM
74LVC1G125GS	VM

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

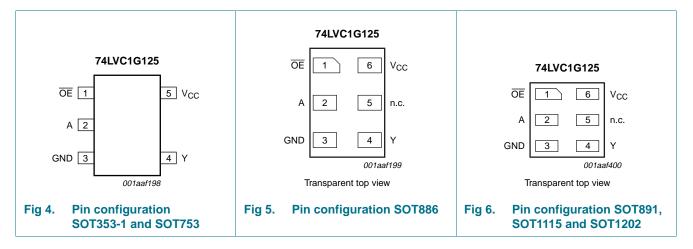
5. Functional diagram



74LVC1G125 Product data sheet

6. Pinning information

6.1 Pinning



6.2 Pin description

Symbol	Pin		Description	
	SOT353-1, SOT753	SOT886, SOT891, SOT1115, SOT1202		
E	1	1	output enable input	
	2	2	data input	
ND	3	3	ground (0 V)	
	4	4	data output	
) .	-	5	not connected	
	5	6	supply voltage	

7. Functional description

Table 4. Function table^[1]

Input OE A		Output
OE	Α	Y
L	L	L
L	Н	Н
Н	Х	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V	-	±50	mA
Vo	output voltage	Active mode	<u>[1][2]</u> –0.5	V _{CC} + 0.5	V
		Power-down mode	<u>[1][2]</u> –0.5	+6.5	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	<u>[3]</u>	250	mW
T _{stg}	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	V _{CC}	V
		$V_{CC} = 0 V$; Power-down mode	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		$V_{CC} = 2.7 \text{ V} \text{ to } 5.5 \text{ V}$	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -	40 °C to +85 °C					
VIH	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$: -	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		V_{CC} = 1.65 V to 5.5 V; I_O = 100 μA	-	-	0.1	V
		V _{CC} = 1.65 V; I _O = 4 mA	-	-	0.45	V
		$V_{CC} = 2.3 \text{ V}; I_{O} = 8 \text{ mA}$	-	-	0.3	V
		$V_{CC} = 2.7 \text{ V}; I_{O} = 12 \text{ mA}$	-	-	0.4	V
		$V_{CC} = 3.0 \text{ V}; I_{O} = 24 \text{ mA}$	-	-	0.55	V
		$V_{CC} = 4.5 \text{ V}; I_{O} = 32 \text{ mA}$	-	-	0.55	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		V_{CC} = 1.65 V to 5.5 V; I_O = –100 μA	$V_{CC}-0.1$	-	-	V
		V_{CC} = 1.65 V; I _O = -4 mA	1.2	-	-	V
		$V_{CC} = 2.3 \text{ V}; I_{O} = -8 \text{ mA}$	1.9	-	-	V
		V_{CC} = 2.7 V; I _O = -12 mA	2.2	-	-	V
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{O} = -24 \text{ mA}$	2.3	-	-	V
		V_{CC} = 4.5 V; I _O = -32 mA	3.8	-	-	V
1	input leakage current	V_{CC} = 0 V to 5.5 V; V_{I} = 5.5 V or GND	-	±0.1	±5	μΑ
oz	OFF-state output current	V_{CC} = 3.6 V; V_I = V_{IH} or V_{IL} ; V_O = 5.5 V or GND	-	±0.1	±10	μA
OFF	power-off leakage current	V_{CC} = 0 V; V _I or V _O = 5.5 V	-	±0.1	±10	μΑ
СС	supply current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_O = 0 \text{ A}$	-	0.1	10	μA
∆l _{CC}	additional supply current	per pin; V _{CC} = 2.3 V to 5.5 V; V _I = V _{CC} – 0.6 V; I _O = 0 A	-	5	500	μA
Cı	input capacitance		-	5	-	pF

Bus buffer/line driver; 3-state

	Parameter	s; voltages are referenced to GND (ground Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
-		Conditions	IVIIII	турш	IVIAX	Unit
	40 °C to +125 °C		0.05 1/			
VIH	HIGH-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	$0.7\times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		V_{CC} = 1.65 V to 5.5 V; I_O = 100 μA	-	-	0.1	V
		V _{CC} = 1.65 V; I _O = 4 mA	-	-	0.70	V
		$V_{CC} = 2.3 \text{ V}; I_{O} = 8 \text{ mA}$	-	-	0.45	V
		$V_{CC} = 2.7 \text{ V}; I_{O} = 12 \text{ mA}$	-	-	0.60	V
		$V_{CC} = 3.0 \text{ V}; I_{O} = 24 \text{ mA}$	-	-	0.80	V
		V _{CC} = 4.5 V; I _O = 32 mA	-	-	0.80	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		V_{CC} = 1.65 V to 5.5 V; I_O = -100 μ A	$V_{CC} - 0.1$	-	-	V
		$V_{CC} = 1.65 \text{ V}; I_{O} = -4 \text{ mA}$	0.95	-	-	V
		$V_{CC} = 2.3 \text{ V}; I_{O} = -8 \text{ mA}$	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V}; I_{O} = -12 \text{ mA}$	1.9	-	-	V
		$V_{CC} = 3.0 \text{ V}; I_{O} = -24 \text{ mA}$	2.0	-	-	V
		$V_{CC} = 4.5 \text{ V}; I_{O} = -32 \text{ mA}$	3.4	-	-	V
I	input leakage current	$V_{CC} = 0 V$ to 5.5 V; $V_{I} = 5.5 V$ or GND	-	-	±100	μA
l _{oz}	OFF-state output current	$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = \text{V}_{IH} \text{ or } \text{V}_{IL};$	-	-	±200	μA
02		$V_0 = 5.5 \text{ V or GND}$				··· ·
I _{OFF}	power-off leakage current	V_{CC} = 0 V; V _I or V _O = 5.5 V	-	-	±200	μA
I _{CC}	supply current	$V_{I} = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to 5.5 V; }I_{O} = 0 \text{ A}$	-	-	200	μΑ
ΔI_{CC}	additional supply current	per pin; $V_{CC} = 2.3 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}$	-	-	5000	μΑ

Table 7. Static characteristics ... continued

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see <u>Figure 9</u>.

Symbol Parameter		Conditions		−40 °C to +85 °C			–40 °C to	Unit	
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	A to Y; see Figure 7	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.3	8.0	1.0	10.5	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.2	5.5	0.5	7	ns
		$V_{CC} = 2.7 V$		0.5	2.5	5.5	0.5	7	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.1	4.5	0.5	6	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.7	4.0	0.5	5.5	ns
t _{en}	enable time	OE to Y; see Figure 8	[3]						
		V_{CC} = 1.65 V to 1.95 V		1.0	4.1	9.4	1.0	12	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.8	6.6	0.5	8.5	ns
		$V_{CC} = 2.7 V$		0.5	3.3	6.6	0.5	8.5	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.4	5.3	0.5	7	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.1	5.0	0.5	6.5	ns
t _{dis}	disable time	OE to Y; see Figure 8	[4]						
		V_{CC} = 1.65 V to 1.95 V		1.0	4.3	9.2	1.0	12	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.7	5.0	0.5	6.5	ns
		$V_{CC} = 2.7 V$		0.5	3.0	5.0	0.5	6.5	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	3.1	5.0	0.5	6.5	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.2	4.2	0.5	5.5	ns
C _{PD}	power dissipation	per buffer; V_I = GND to V_{CC}	[5]						
	capacitance	output enabled		-	25	-	-	-	pF
		output disabled		-	6	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

- [3] $t_{en} \mbox{ is the same as } t_{PZH} \mbox{ and } t_{PZL}$
- $\label{eq:tdis} \begin{tabular}{c} [4] & t_{dis} \ is the same as t_{PLZ} and t_{PHZ} \end{tabular}$
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).
 - $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

f_i = input frequency in MHz;

 f_o = output frequency in MHz;

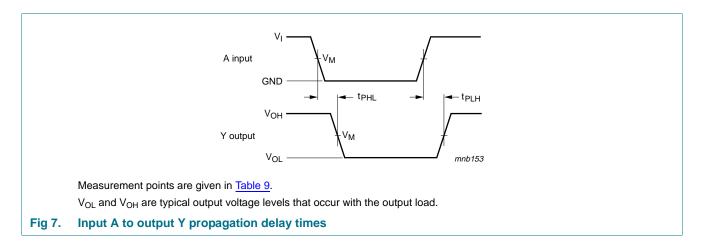
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

Bus buffer/line driver; 3-state

12. Waveforms



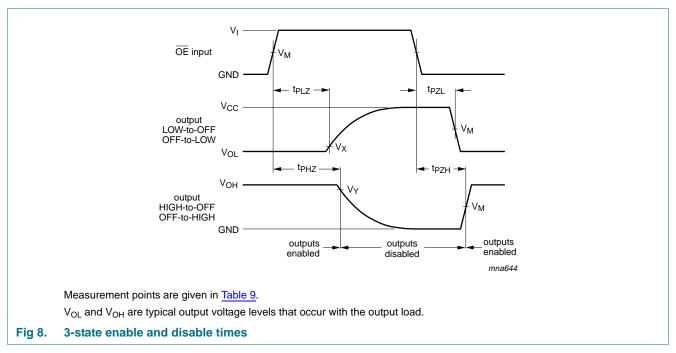


Table 9. Measurement points

Supply voltage	Input	Output		
V _{CC}	V _M	V _M	V _X	V _Y
1.65 V to 1.95 V	0.5V _{CC}	$0.5V_{CC}$	V _{OL} + 0.15 V	$V_{OH} - 0.15 \ V$
2.3 V to 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$	V _{OL} + 0.15 V	V _{OH} – 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$
4.5 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$

74LVC1G125 Product data sheet

Bus buffer/line driver; 3-state

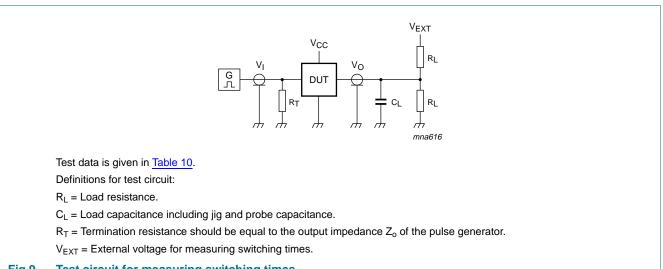


Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	ly voltage Input		Load		Load V _{EX}		V _{EXT}		
V _{CC}	VI	t _r , t _f	CL	RL	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open	GND	2V _{CC}		
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	open	GND	$2V_{CC}$		
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open	GND	6 V		
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open	GND	6 V		
4.5 V to 5.5 V	V _{CC}	\leq 2.5 ns	50 pF	500 Ω	open	GND	$2V_{CC}$		

Bus buffer/line driver; 3-state

13. Package outline

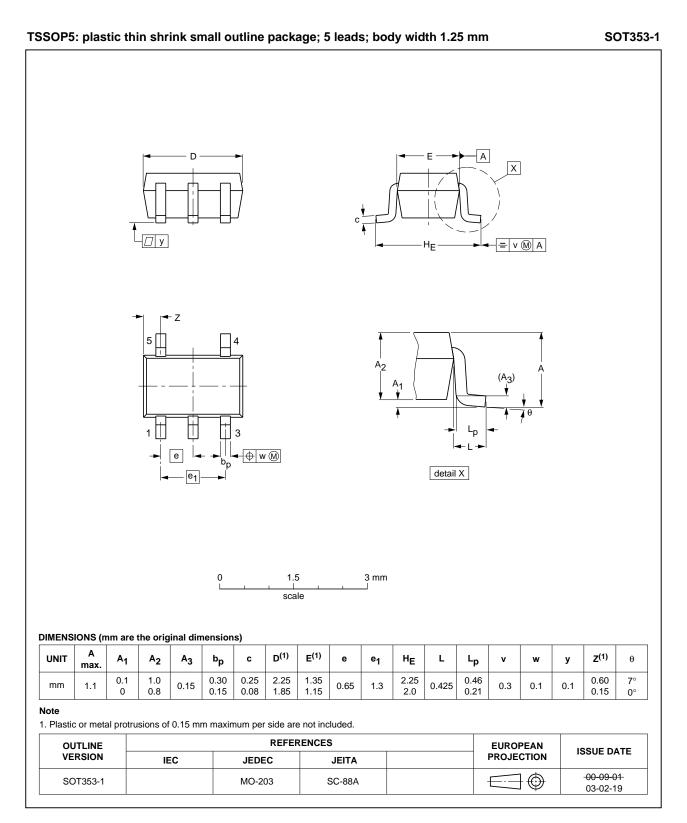


Fig 10. Package outline SOT353-1 (TSSOP5)

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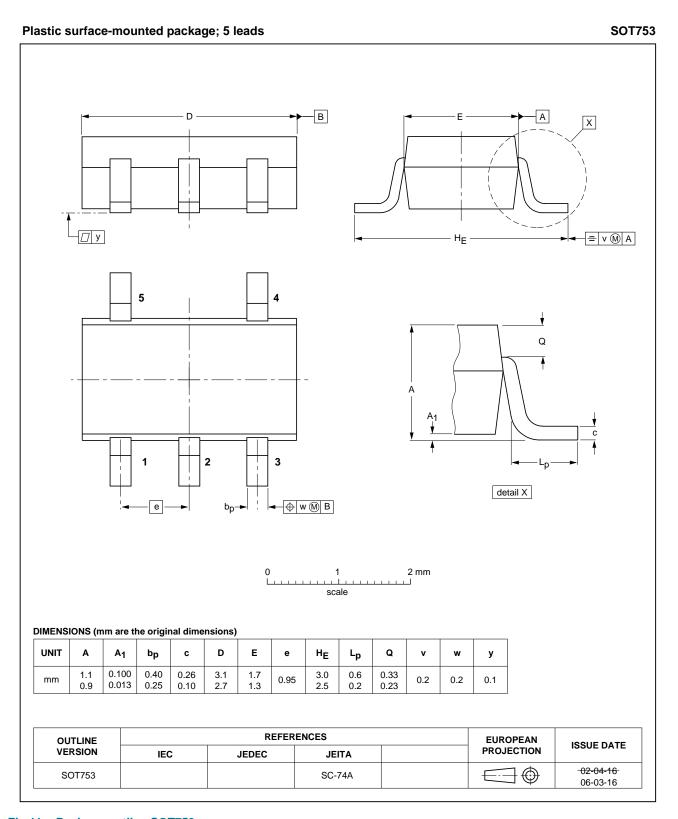
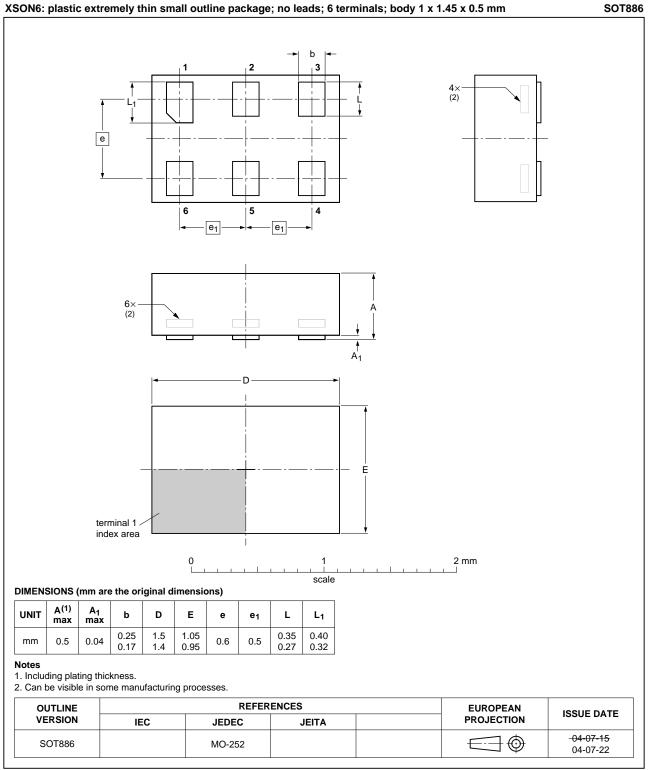


Fig 11. Package outline SOT753

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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

Fig 12. Package outline SOT886 (XSON6)

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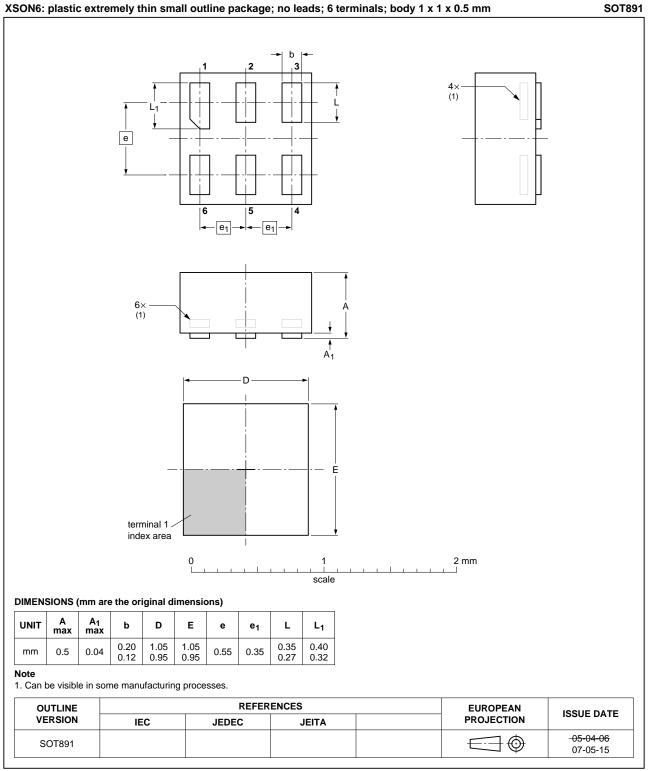
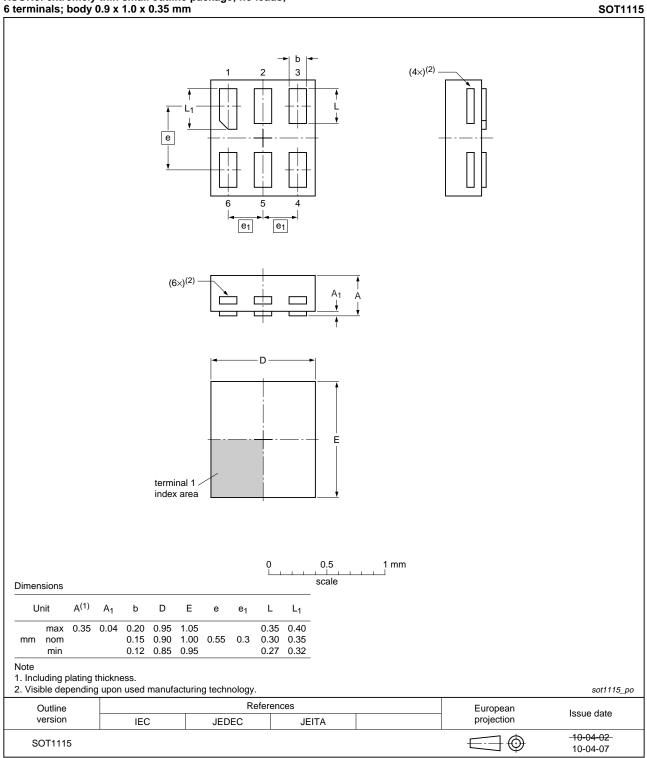
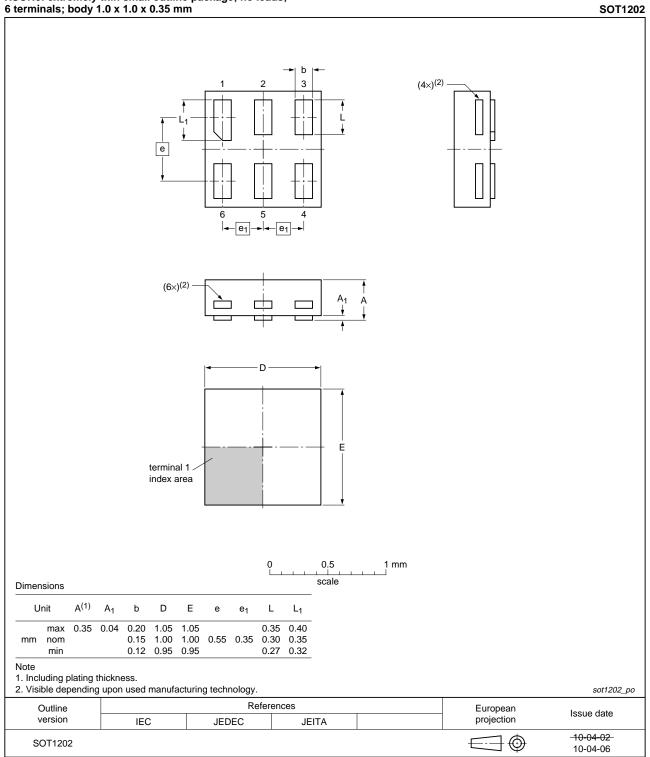


Fig 13. Package outline SOT891 (XSON6)



XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1115 (XSON6)



XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1202 (XSON6)



14. Abbreviations

AcronymDescriptionCMOSComplementary Metal Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Table 11.	Abbreviations
DUT Device Under Test ESD ElectroStatic Discharge HBM Human Body Model	Acronym	Description
ESD ElectroStatic Discharge HBM Human Body Model	CMOS	Complementary Metal Oxide Semiconductor
HBM Human Body Model	DUT	Device Under Test
	ESD	ElectroStatic Discharge
MM Machine Model	HBM	Human Body Model
	MM	Machine Model
TTL Transistor-Transistor Logic	TTL	Transistor-Transistor Logic

15. Revision history

Table 12. **Revision history** Document ID **Release date** Data sheet status **Change notice Supersedes** 74LVC1G125 v.9 20101229 Product data sheet 74LVC1G125 v.8 _ Modifications: Minimum limit V_{OH} at a supply voltage of 3.0 V changed from 2.7 V to 2.3 V. 74LVC1G125 v.8 20100824 Product data sheet 74LVC1G125 v.7 Modifications: Added type number 74LVC1G125GN (SOT1115/XSON6 package). Added type number 74LVC1G125GS (SOT1202/XSON6 package). 74LVC1G125 v.7 20070830 Product data sheet -74LVC1G125 v.6 74LVC1G125 v.6 Product data sheet 74LVC1G125 v.5 20060912 -74LVC1G125 v.4 74LVC1G125 v.5 20040915 Product specification _ 74LVC1G125 v.4 74LVC1G125 v.3 20021118 Product specification -74LVC1G125 v.3 74LVC1G125 v.2 20020528 Product specification -74LVC1G125 v.2 20010406 Product specification -74LVC1G125 v.1 74LVC1G125 v.1 20001222 Product specification -_

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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74LVC1G125 Product data sheet

Bus buffer/line driver; 3-state

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